

MOSFET – N-Channel, POWERTRENCH®

80 V, 100 A, 4.2 mΩ

FDD86367

Features

- Typical $R_{DS(on)} = 3.3\text{ m}\Omega$ at $V_{GS} = 10\text{ V}$, $I_D = 80\text{ A}$
- Typical $Q_{g(tot)} = 68\text{ nC}$ at $V_{GS} = 10\text{ V}$, $I_D = 80\text{ A}$
- UIS Capability
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

- PowerTrain Management
- Solenoid and Motor Drivers
- Integrated Starter/Alternator
- Primary Switch for 12 V Systems

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Ratings | Unit |
|-----------------|-------------------------------------------------------------|-----------------|---------------------------|
| V_{DS} | Drain-to-Source Voltage | 80 | V |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| I_D | Drain Current – Continuous ($V_{GS} = 10$) (Note 1) | 100 | A |
| | Pulsed Drain Current $T_C = 25^\circ\text{C}$ | See Figure 4 | |
| EAS | Single Pulse Avalanche Energy (Note 2) | 82 | mJ |
| P_D | Power Dissipation | 227 | W |
| | Derate Above 25°C | 1.52 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Temperature | -55 to $+175$ | $^\circ\text{C}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 0.66 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Maximum Thermal Resistance, Junction to Ambient (Note 3) | 52 | $^\circ\text{C}/\text{W}$ |

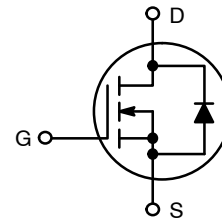
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by bondwire configuration.
2. Starting $T_J = 25^\circ\text{C}$, $L = 40\text{ }\mu\text{H}$, $I_{AS} = 64\text{ A}$, $V_{DD} = 80\text{ V}$ during inductor charging and $V_{DD} = 0\text{ V}$ during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

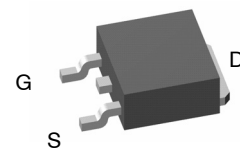


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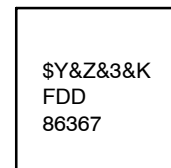


N-Channel



DPAK3 (TO-252 3 LD)
CASE 369AS

MARKING DIAGRAM



FDD86367 = Specific Device Code
 \$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = 3-Digit Date Code
 &K = 2-Digits Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

PACKAGE MARKING AND ORDERING INFORMATION

| Device | Device Marking | Package | Reel Size | Tape Width | Shipping† |
|----------|----------------|-----------------------------------|-----------|------------|--------------------|
| FDD86367 | FDD86367 | DDPAK3 (TO-252 3 LD) (Pb-Free) | 13" | 16 mm | 2500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|--------|-----------|-----------|-----|-----|-----|------|
|--------|-----------|-----------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | | |
|--------------|-----------------------------------|-----------------------------------------------|------------------------------------|---|-----------|----|----|
| $B_{V_{DS}}$ | Drain-to-Source Breakdown Voltage | $I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$ | 80 | - | - | V | |
| I_{DSS} | Drain-to-Source Leakage Current | $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$ | $T_J = 25^\circ\text{C}$ | - | - | 1 | mA |
| | | | $T_J = 175^\circ\text{C}$ (Note 4) | - | - | 1 | mA |
| I_{GSS} | Gate-to-Source Leakage Current | $V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA | |

ON CHARACTERISTICS

| | | | | | | | |
|--------------|----------------------------------|---------------------------------------------|------------------------------------|---|-----|-----|------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$ | 2 | 3 | 4 | V | |
| $R_{DS(on)}$ | Drain to Source On Resistance | $I_D = 80 \text{ A}, V_{GS} = 10 \text{ V}$ | $T_J = 25^\circ\text{C}$ | - | 3.3 | 4.2 | m Ω |
| | | | $T_J = 175^\circ\text{C}$ (Note 4) | - | 6.6 | 8.4 | m Ω |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|--------------|-------------------------------|------------------------------------------------------------------|---|------|----|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | - | 4840 | - | pF |
| C_{oss} | Output Capacitance | | - | 814 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 31 | - | pF |
| R_g | Gate Resistance | $V_{GS} = 0.5 \text{ V}, f = 1 \text{ MHz}$ | - | 2.3 | - | Ω |
| $Q_{g(TOT)}$ | Total Gate Charge | $V_{GS} = 0 \text{ to } 10 \text{ V}$ | - | 68 | 88 | nC |
| $Q_{g(th)}$ | Threshold Gate Charge | $V_{GS} = 0 \text{ to } 2 \text{ V}$ | | | | |
| Q_{gs} | Gate-to-Source Gate Charge | $V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}$ | - | 22 | - | nC |
| Q_{gd} | Gate-to-Drain "Miller" Charge | | - | 14 | - | nC |

SWITCHING CHARACTERISTICS

| | | | | | | |
|--------------|----------------|----------------------------------------------------------------------------------------|---|----|-----|----|
| t_{on} | Turn-On Time | $V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}, V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$ | - | - | 104 | ns |
| $t_{d(on)}$ | Turn-On Delay | | - | 20 | - | ns |
| t_r | Rise Time | | - | 49 | - | ns |
| $t_{d(off)}$ | Turn-Off Delay | | - | 36 | - | ns |
| t_f | Fall Time | | - | 16 | - | ns |
| t_{off} | Turn-Off Time | | - | - | 80 | ns |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | |
|----------|-------------------------------|-------------------------------------------------------------------------------------|---|----|-----|----|
| V_{SD} | Source-to-Drain Diode Voltage | $I_{SD} = 80 \text{ A}, V_{GS} = 0 \text{ V}$ | - | - | 1.3 | V |
| | | $I_{SD} = 40 \text{ A}, V_{GS} = 0 \text{ V}$ | - | - | 1.2 | V |
| t_{rr} | Reverse-Recovery Time | $V_{DD} = 64 \text{ V}, I_F = 80 \text{ A}, dI_{SD}/dt = 100 \text{ A}/\mu\text{s}$ | - | 68 | 102 | ns |
| Q_{rr} | Reverse-Recovery Charge | | - | 66 | 106 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production.

TYPICAL CHARACTERISTICS

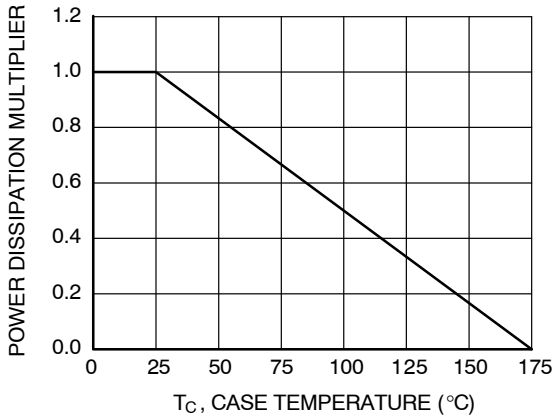


Figure 1. Normalized Power Dissipation vs. Case Temperature

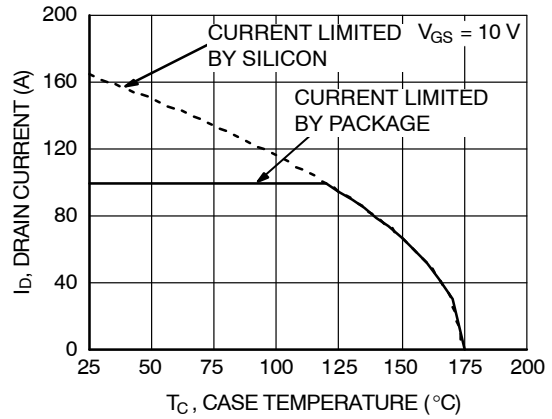


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

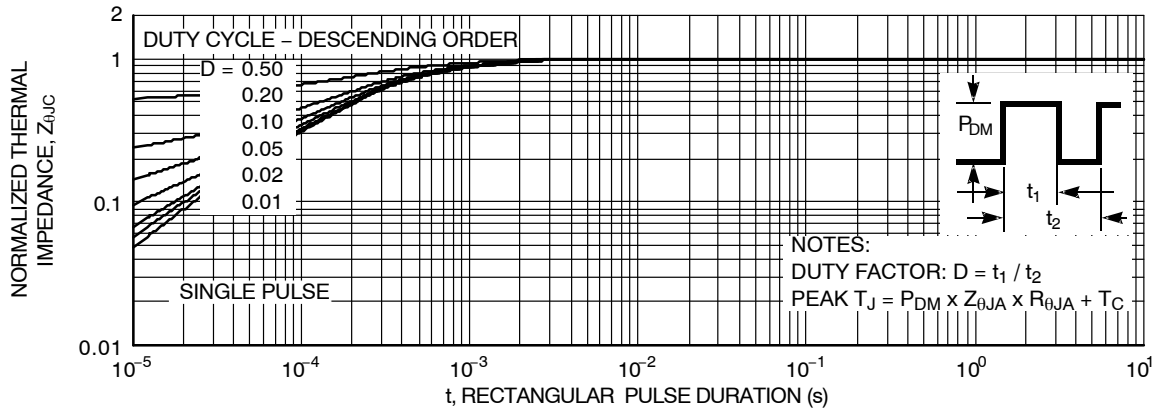


Figure 3. Normalized Maximum Transient Thermal Impedance

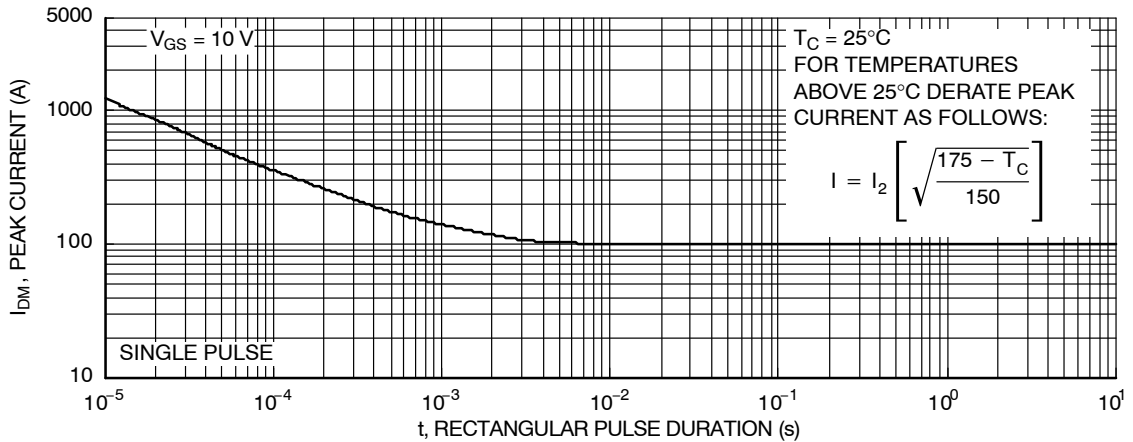


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS (continued)

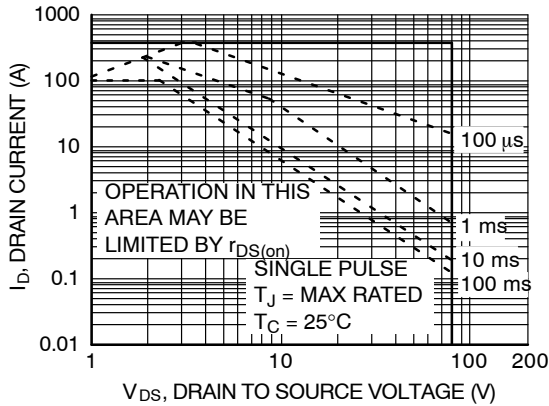
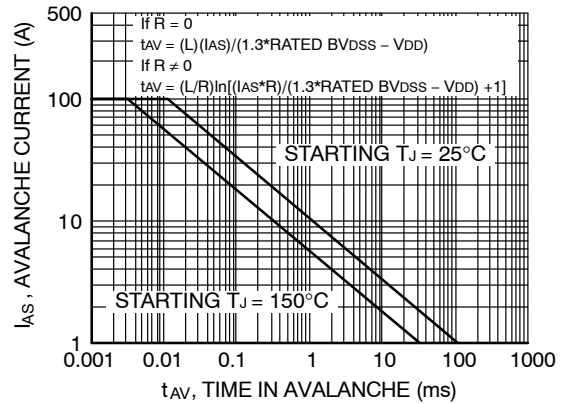


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Application Notes [AN7514](#) and [AN7515](#)

Figure 6. Unclamped Inductive Switching Capability

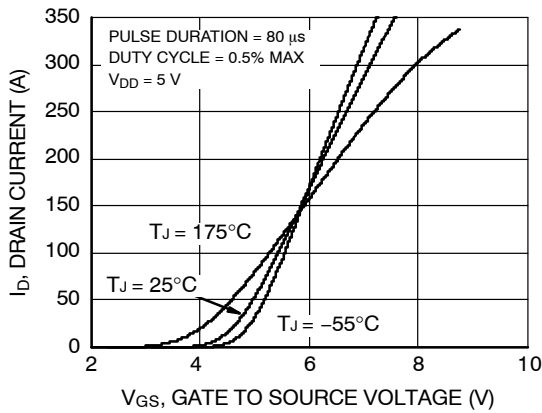


Figure 7. Transfer Characteristics

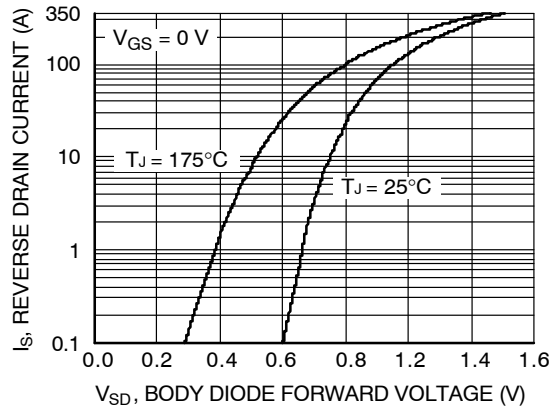


Figure 8. Forward Diode Characteristics

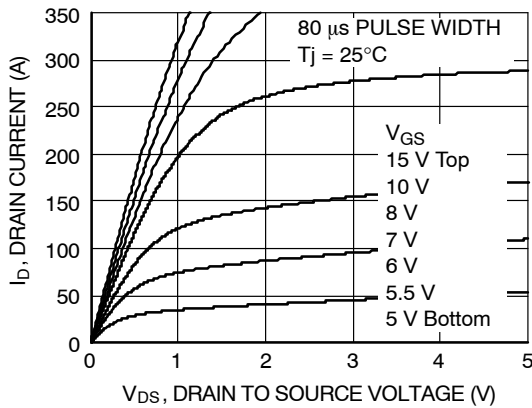


Figure 9. Saturation Characteristics

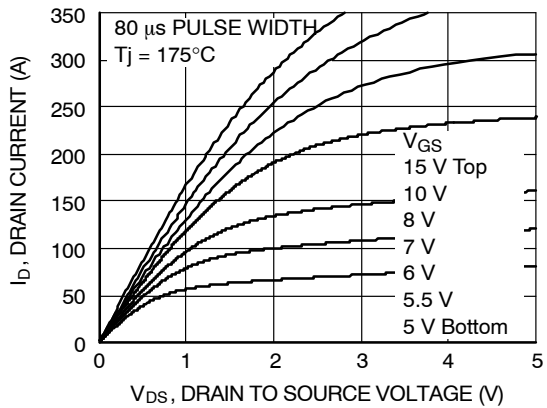


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (continued)

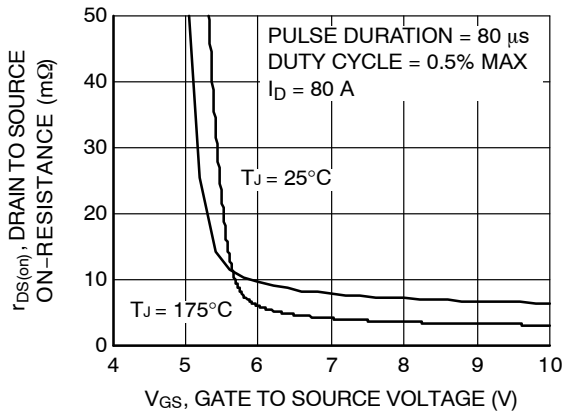


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

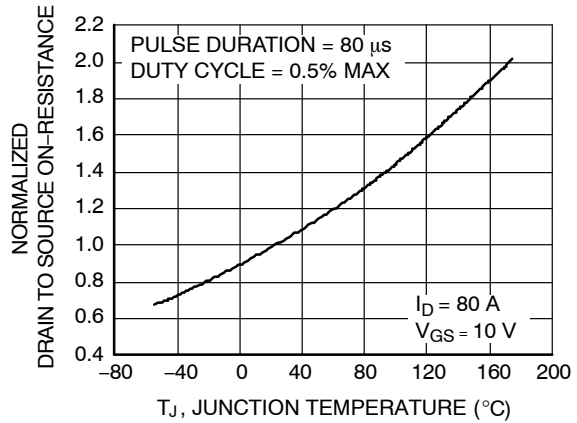


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

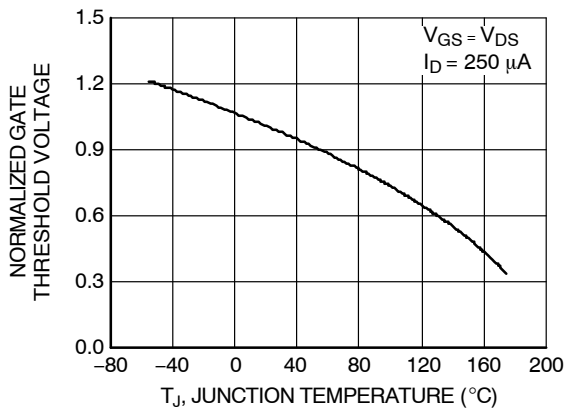


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

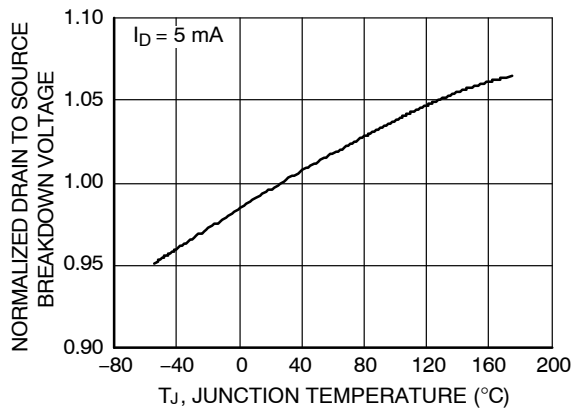


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

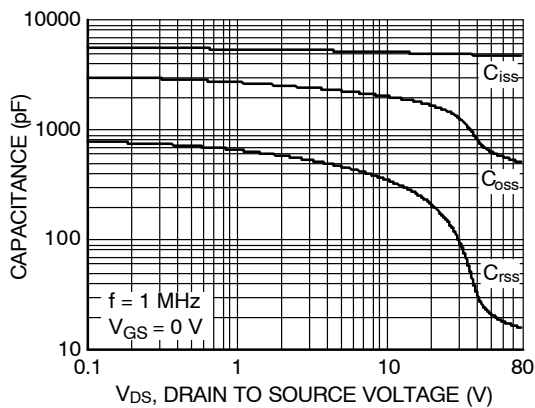


Figure 15. Capacitance vs. Drain to Source Voltage

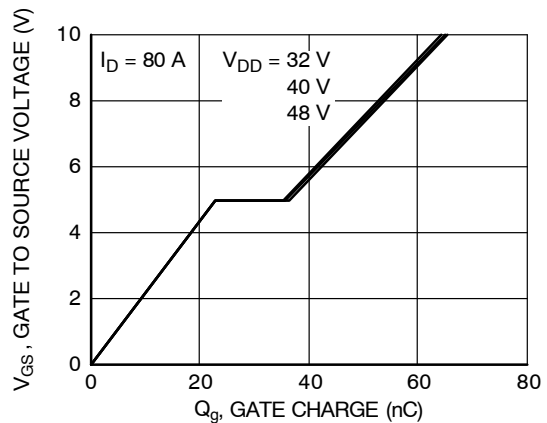


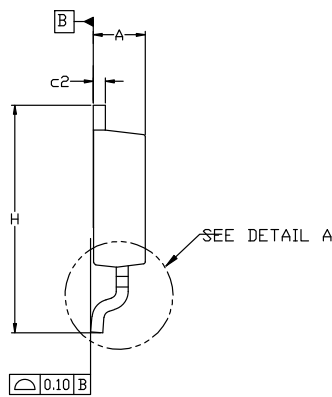
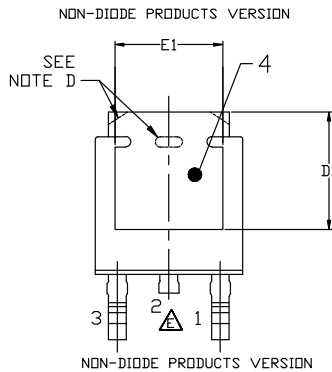
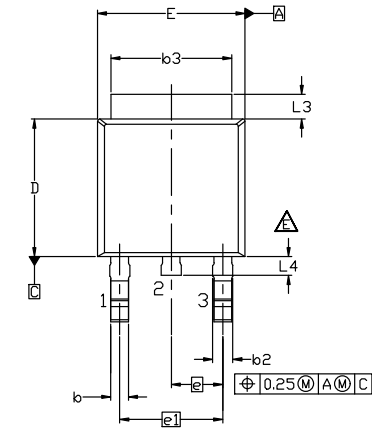
Figure 16. Gate Charge vs. Gate to Source Voltage

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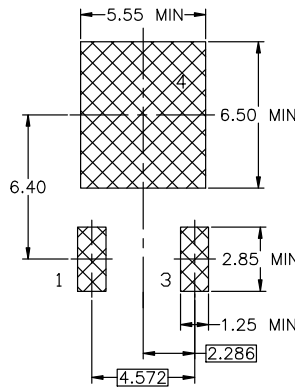
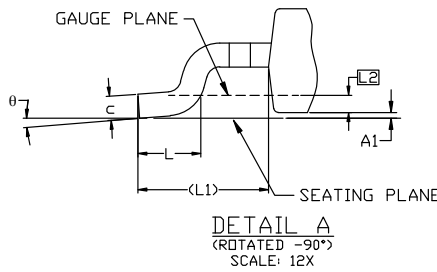


**DPAK3 6.10x6.54x2.29, 4.57P
CASE 369AS
ISSUE B**

DATE 20 DEC 2023



- NOTES: UNLESS OTHERWISE SPECIFIED
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2018.
 D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 E) FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY STUB WITHOUT CENTER LEAD.
 F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TD228P991X239-3N.

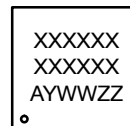


LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

| DIM | MILLIMETERS | | |
|-----|-------------|------|-------|
| | MIN. | NOM. | MAX. |
| A | 2.18 | 2.29 | 2.39 |
| A1 | 0.00 | - | 0.127 |
| b | 0.64 | 0.77 | 0.89 |
| b2 | 0.76 | 0.95 | 1.14 |
| b3 | 5.21 | 5.34 | 5.46 |
| c | 0.45 | 0.53 | 0.61 |
| c2 | 0.45 | 0.52 | 0.58 |
| D | 5.97 | 6.10 | 6.22 |
| D1 | 5.21 | --- | --- |
| E | 6.35 | 6.54 | 6.73 |
| E1 | 4.32 | --- | --- |
| e | 2.286 BSC | | |
| e1 | 4.572 BSC | | |
| H | 9.40 | 9.91 | 10.41 |
| L | 1.40 | 1.59 | 1.78 |
| L1 | 2.90 REF | | |
| L2 | 0.51 BSC | | |
| L3 | 0.89 | 1.08 | 1.27 |
| L4 | --- | --- | 1.02 |
| θ | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

| | | |
|-------------------------|------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION: | DPAK3 6.10x6.54x2.29, 4.57P | PAGE 1 OF 1 |

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